

Edited by Bill Travis

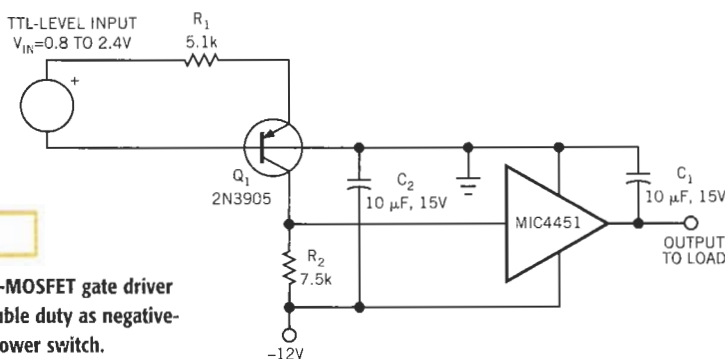
## Build a negative-voltage power-side switch

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**W**HEN YOU NEED to quickly connect a negative power supply under logic control, the negative power-side switch in **Figure 1** can help. Although originally intended for driving the gates of high-current MOSFETs, the MIC4451 can assume a different role. It provides complementary, low-on-resistance MOSFET switches to connect a system power-supply rail to a negative input voltage or to ground, enabled by a digital signal. The MIC4451 comprises an input buffer with a small amount of hysteresis and several logic inverter/buffers that ultimately drive a high-current output stage. **Figure 2** shows a block diagram of the MIC4451. The on-resistance of the n- and p-channel

**Figure 1**

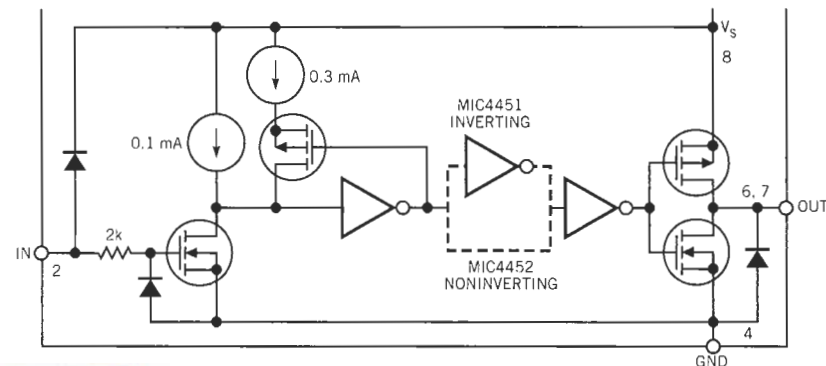
A power-MOSFET gate driver does double duty as negative-supply power switch.



devices at the output is approximately 1Ω. So, the output can connect a 100-mA load to the negative input voltage with less than 100-mV voltage drop. A noninverting version, the MIC4452, sim-

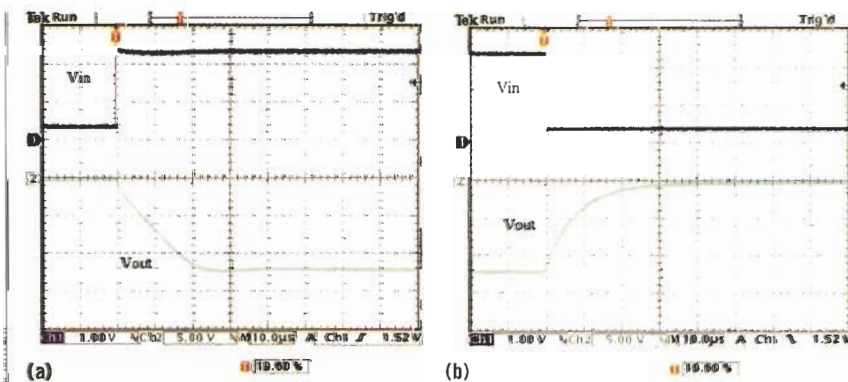
plifies inversion of logic control as needed. **Figure 1** shows details of the interface of the MIC4451 to TTL levels, using a common-base pnp transistor for level translation. The emitter current of Q<sub>1</sub> is approximately:  $I_E = (V_{TTLH} - V_{BE})/R_1 \approx (2.4 - 0.65)/R_1$ , where  $V_{TTLH}$  is the TTL-high level, 2.4V.  $I_E$  should be  $\leq 400 \mu A$  in accordance with TTL specs, so  $I_E = (2.4 - 0.65)/R_1 \leq 400 \mu A$ .

Solving for  $R_1$ , you obtain  $R_1 \geq 1.8V/400 \mu A = 4.5 k\Omega$ . The  $V_{IH}$  (lowest permissible high input) logic-level specification of the MIC4451 is 2.4V. Ignoring base-current errors,  $I_C \approx I_E$ , so  $R_2 I_C \geq 2.4V$ . Note that the MIC4451's input voltage,  $V_{IH}$ , is specified with respect to the ground pin of the part. To determine  $R_2$ :  $R_2 = 2.4V/I_C$



**Figure 2**

The MIC445x FET driver includes low-on-resistance complementary FETs.



**Figure 3**

Turn-on (a) and turn-off (b) characteristics of the circuit in **Figure 1** are for a -12V supply.

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detector. The power switch and series-connected power rectifier,  $D_1$ , protect the load against high-voltage transients and continuous over-voltage as high as  $\pm 500V$  of either polarity.

In the circuit, which powers loads as heavy as 1A from a nominal 12V power line, a high-side-switch driver,  $IC_1$ , biases the power switch fully on. You can increase the maximum load current by changing  $D_1$  and  $Q_1$ . To guard against low supply voltage,  $IC_1$  includes an undervoltage-lockout feature that allows operation only when the line voltage is greater than 10V. To protect against overvoltage, the circuit includes a three-transistor, no-bias-current, 50-nsec-operation over-voltage detector that triggers when the input voltage reaches approximately 20V. At that time,  $Q_4$  "crowbars" the gate of the

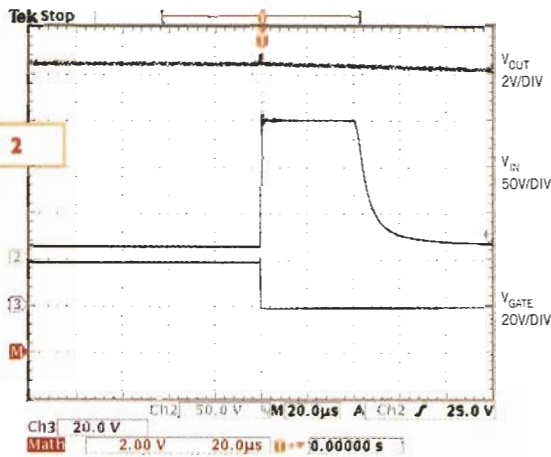
power switch to ground, turning it off hard. Rising overvoltage first turns on zener diode  $D_2$ , which protects the IC by clamping the voltage across it to approximately 18V. Zener current flows through the 2.2-k $\Omega$  resistor, producing a base voltage that turns on  $Q_2$ . That action ini-

tiates a rapid sequence:  $Q_3$  turns on, which turns on  $Q_4$ , which turns off  $Q_1$  by quickly discharging its gate capacitance.

You can demonstrate the circuit's performance by applying a 150V transient to the supply voltage while the circuit output is delivering 1A at 12V (Figure 2). The internal impedance of the transient source is 1 $\Omega$ , and the rise time of the applied voltage is 1  $\mu$ sec. The circuit draws 20  $\mu$ A during normal operation, including 3  $\mu$ A by the undervoltage-lockout, voltage-sensing divider and 17  $\mu$ A by  $IC_1$ . If your design

needs high-temperature operation, note that the gate-current output of  $IC_1$  is relatively limited. Your design calculations for high temperature should also pay close attention to leakage currents that the other circuit components contribute.  $\square$

Figure 2



A 150V transient applied to  $V_{IN}$  of the Figure 1 circuit has little effect on  $V_{OUT}$ .